



#6/A 2826  
10-9-02  
Mullin

Atty. Docket No. 8005-1004

PATENTS

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Koichi OHTO et al.

Confirmation No. 1071

Serial No. 09/883,370

GROUP 2826

Filed June 19, 2001

Examiner F. Erdem

SEMICONDUCTOR DEVICE AND METHOD  
AND APPARATUS FOR MANUFACTURING  
THE SAME

AMENDMENT

Commissioner for Patents

Washington, D.C. 20231

Sir:

Responsive to the Official Action of July 1, 2002,  
please amend the above-identified application as follows:

IN THE SPECIFICATION:

Page 2, replace the paragraph beginning on line 17 as  
follows:

A<sup>1</sup>  
--When Cu is used as the interconnection material,  
since it is difficult to micropattern Cu by dry etching, a  
damascene interconnection structure as shown in Fig. 1 is usually  
used widely. A damascene interconnection is formed in the  
following manner. A trench is formed in an interlevel film 6,  
and is filled with a barrier metal 10 and Cu. Excessive Cu and  
barrier metal on the insulating film are removed by CMP, thus  
forming a Cu interconnection 12.--